

SOD-323 Plastic-Encapsulate ESD Protection Diodes

DESCRIPTION

The ESD3B3CM is designed to protect voltage sensitive components from ESD and transient voltage events. Excellent clamping capability, low leakage, and fast response time, make these parts ideal for ESD protection on designs where board space is at a premium. Because of its small size, it is suited for use in cellular phones, portable devices, digital cameras, power supplies and many other portable applications where board space comes at a premium. Also because of its low capacitance, it is suited for use in high frequency designs such as high speed line applications.

This device has been specifically designed to protect sensitive components which are connected to data and transmission lines from overvoltage caused by ESD (electrostatic discharge), and EFT (electrical fast transients).

Features

- ◆ Peak power dissipation: 500W (8/20μs)
- ◆ IEC61000-4-2 (ESD) ±30kV (air), ±30kV (contact)
- ◆ IEC61000-4-4 (EFT) 40A (5/50ns)
- ◆ Protects one Vcc or data line
- ◆ Low clamping voltage
- ◆ Low leakage current
- ◆ Low capacitance
- ◆ Working voltages : 3.3V
- ◆ Meets MSL 1 Requirements

Pin Configuration



Cir



- ◆ Cell Phone Handsets and Accessories
- ◆ Microprocessor based equipment
- ◆ Personal Digital Assistants (PDA's)
- ◆ Notebooks, Desktops, and Servers
- ◆ Portable Instrumentation
- ◆ Networking and Telecom
- ◆ Serial and Parallel Ports
- ◆ Peripherals

- ◆ Marking: 2A

Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
ESD per IEC 61000-4-2 (Air)	VESD	± 30	KV
ESD per IEC 61000-4-2 (Contact)		± 30	
Peak Pulse Power(8/20us)	PPP	500	W
Operating Temperature	T _{OPT}	-55 to +150	°C
Storage Temperature	T _{STG}	-55 to +150	°C

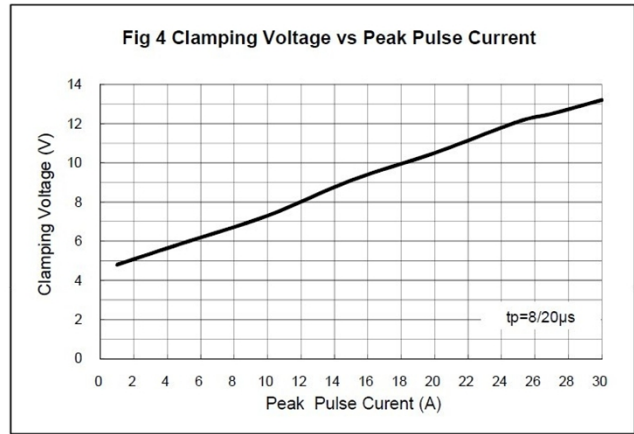
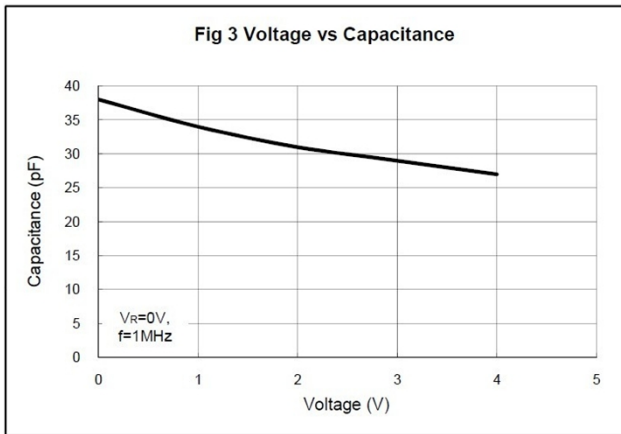
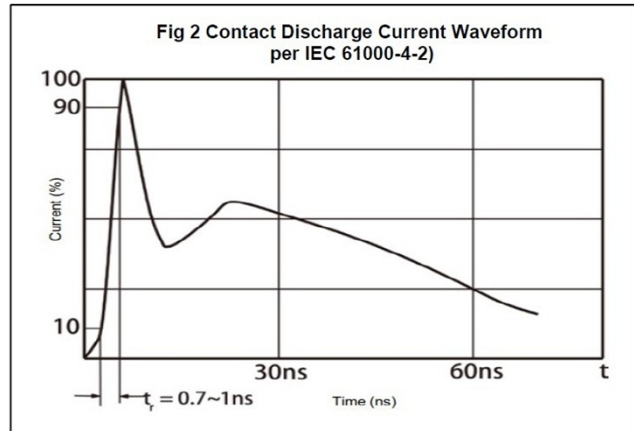
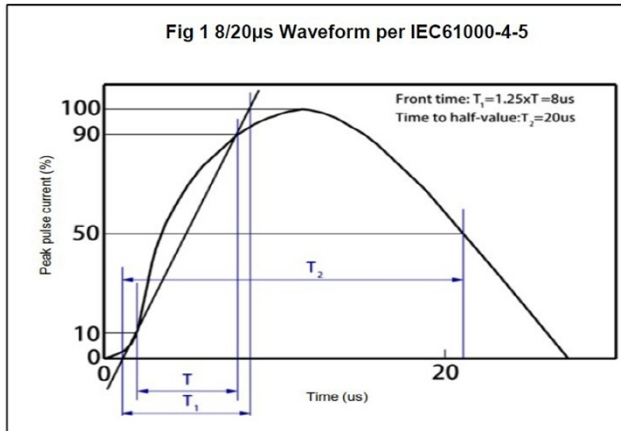
The above data are for reference only.

Electrical Characteristics (TA=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min	Typ	Max	Units
V_{RWM}	Reverse Working Voltage				3.3	V
V_{BR}	Reverse Breakdown Voltage	$I_T = 1mA$	4.0		6.0	V
I_R	Reverse Leakage Current	$V_{RWM} = 3.3V$			1.0	μA
V_C	Clamping Voltage	$I_{PP} = 1A, t_p = 8/20\mu s$			6.5	V
V_C	Clamping Voltage	$I_{PP} = 28A, t_p = 8/20\mu s$		13	18	V
C_J	Junction Capacitance	$V_R = 0V, f = 1MHz$		30	45	pF

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ELECTRICAL CHARACTERISTICS CURVE



The curve above is for reference only.